

## A2G30N1200MT7 1200V N-Channel MOSFET

### Description

Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

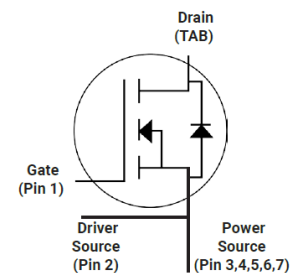
### Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Optimized package with separate driver source pin
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free



### Application

- EV Charging
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Power Factor Correction Modules



### Ordering Information

| Part Number   | Marking       | Package  | Packaging |
|---------------|---------------|----------|-----------|
| A2G30N1200MT7 | A2G30N1200MT7 | TO-263-7 | Tube      |

**Absolute Maximum Ratings(Tc=25°C)**

| Symbol                | Parameter                               | Value       | Unit |
|-----------------------|-----------------------------------------|-------------|------|
| V <sub>DS</sub>       | Drain-Source Voltage                    | 1200        | V    |
| I <sub>D</sub>        | Drain Current(continuous)at Tc=25°C     | 32          | A    |
| I <sub>D</sub>        | Drain Current(continuous)at Tc=100°C    | 23          | A    |
| I <sub>DM</sub>       | Drain Current (pulsed)                  | 80          | A    |
| V <sub>GS</sub>       | Gate-Source Voltage                     | -10/+25     | V    |
| P <sub>D</sub>        | Power Dissipation T <sub>C</sub> = 25°C | 145         | W    |
| T <sub>J</sub> , Tstg | Junction and Storage Temperature Range  | -55 to +150 | °C   |

**Electrical Characteristics(T<sub>J</sub> = 25°C unless otherwise specified)**
**Typical Performance-Static**

| Symbol               | Parameter                         | Test Conditions                                                      | Min. | Typ. | Max. | Unit |
|----------------------|-----------------------------------|----------------------------------------------------------------------|------|------|------|------|
| BV <sub>DS</sub>     | Drain-source Breakdown Voltage    | I <sub>D</sub> =250uA, V <sub>GS</sub> =0V                           | 1200 |      |      | V    |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current   | V <sub>DS</sub> =1200V,<br>V <sub>GS</sub> =0V, T <sub>J</sub> =25°C |      |      | 100  | uA   |
| I <sub>GSS</sub>     | Gate-body Leakage Current         | V <sub>DS</sub> =0V ; V <sub>GS</sub> =-10 to 20V                    |      |      | 250  | nA   |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =5mA              | 2    | 3    | 4    | V    |
| V <sub>GS(on)</sub>  | Recommended turn-on Voltage       | Static                                                               |      | 20   |      | V    |
| V <sub>GS(off)</sub> | Recommended turn-off Voltage      |                                                                      |      | -5   |      | V    |
| R <sub>DS(on)</sub>  | Static Drain-source On Resistance | V <sub>GS</sub> =20V, I <sub>D</sub> =20A                            |      | 80   | 100  | mΩ   |
|                      |                                   | V <sub>GS</sub> =20V, I <sub>D</sub> =20A<br>T <sub>J</sub> =150°C   |      | 122  |      | mΩ   |

**Typical Performance-Dynamic**

| Symbol              | Parameter                    | Test Conditions                                                                                             | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|-------------------------------------------------------------------------------------------------------------|------|------|------|------|
| C <sub>iss</sub>    | Input Capacitance            | V <sub>DS</sub> =1000V, f=1MHz,<br>V <sub>AC</sub> =25mV                                                    |      | 1590 |      | pF   |
| C <sub>oss</sub>    | Output Capacitance           |                                                                                                             |      | 63   |      | pF   |
| C <sub>rss</sub>    | Reverse Transfer Capacitance |                                                                                                             |      | 3.9  |      | pF   |
| g <sub>fs</sub>     | Transconductance             | V <sub>DS</sub> =20V, I <sub>D</sub> =20A                                                                   |      | 12   |      | S    |
| E <sub>oss</sub>    | Coss Stored Energy           | V <sub>DS</sub> =1000V, f=1MHz                                                                              |      | 35.7 |      | μJ   |
| E <sub>on</sub>     | Turn-On Energy (Body Diode)  | V <sub>DS</sub> =800V, V <sub>GS</sub> =-5V/20V,<br>I <sub>D</sub> =20A, L=150μH<br>T <sub>J</sub> =150°C   |      | 455  |      | μJ   |
| E <sub>off</sub>    | Turn-Off Energy (Body Diode) |                                                                                                             |      | 111  |      | μJ   |
| Q <sub>g</sub>      | Total Gate Charge            | V <sub>DS</sub> =800V, V <sub>GS</sub> =-5V/20V,<br>I <sub>D</sub> =15A                                     |      | 72   |      | nC   |
| Q <sub>gs</sub>     | Gate-source Charge           |                                                                                                             |      | 21   |      | nC   |
| Q <sub>gd</sub>     | Gate-Drain Charge            |                                                                                                             |      | 22   |      | nC   |
| R <sub>G(int)</sub> | Internal Gate Resistance     | f=1MHz, V <sub>AC</sub> =25mV                                                                               |      | 3    |      | Ω    |
| t <sub>d(on)</sub>  | Turn-on Delay Time           | V <sub>DS</sub> =800V, V <sub>GS</sub> =-5V/20V,<br>I <sub>D</sub> =20A, L=150 μH<br>R <sub>ext</sub> =2.5Ω |      | 42   |      | ns   |
| t <sub>r</sub>      | Rise Time                    |                                                                                                             |      | 15   |      | ns   |
| t <sub>d(off)</sub> | Turn-off Delay Time          |                                                                                                             |      | 36   |      | ns   |
| t <sub>f</sub>      | Fall Time                    |                                                                                                             |      | 11   |      | ns   |

**Typical Performance-Reverse Diode(T<sub>J</sub> = 25°C unless otherwise specified)**

| Symbol           | Parameter                        | Test Conditions                                                                                              | Min. | Typ. | Max. | Unit |
|------------------|----------------------------------|--------------------------------------------------------------------------------------------------------------|------|------|------|------|
| V <sub>FSD</sub> | Forward Voltage                  | V <sub>GS</sub> =0V, I <sub>F</sub> =10A, T <sub>J</sub> =25°C                                               |      | 4.8  | 6    | V    |
|                  |                                  | V <sub>GS</sub> =0V, I <sub>F</sub> =10A, T <sub>J</sub> =150°C                                              |      | 4.2  | 6    | V    |
| I <sub>S</sub>   | Continuous Diode Forward Current | V <sub>GS</sub> =0V, T <sub>C</sub> =25°C                                                                    |      | 27   |      | A    |
| t <sub>rr</sub>  | Reverse Recovery Time            | V <sub>GS</sub> =-5V, I <sub>F</sub> =20A,<br>V <sub>R</sub> =800V, di/dt=900<br>A/μs, T <sub>J</sub> =150°C |      | 36   |      | nS   |
| Q <sub>rr</sub>  | Reverse Recovery Charge          |                                                                                                              |      | 297  |      | nC   |
| I <sub>rrm</sub> | Peak Reverse Recovery Current    |                                                                                                              |      | 15.5 |      | A    |

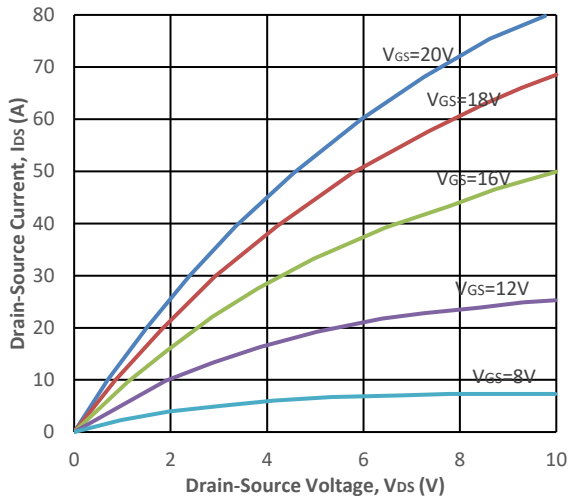
**Thermal Characteristics**

| Symbol           | Parameter                               | Value. | Unit |
|------------------|-----------------------------------------|--------|------|
| R <sub>θJC</sub> | Thermal Resistance, Junction-to-Case    | 0.86   | °C/W |
| R <sub>θJA</sub> | Thermal Resistance, Junction-to-Ambient | 40     | °C/W |

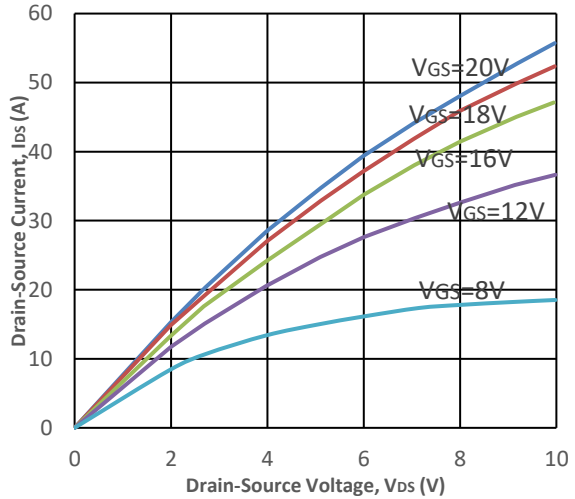
The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of T<sub>J</sub>(max)=150°C

### Electrical Characteristics

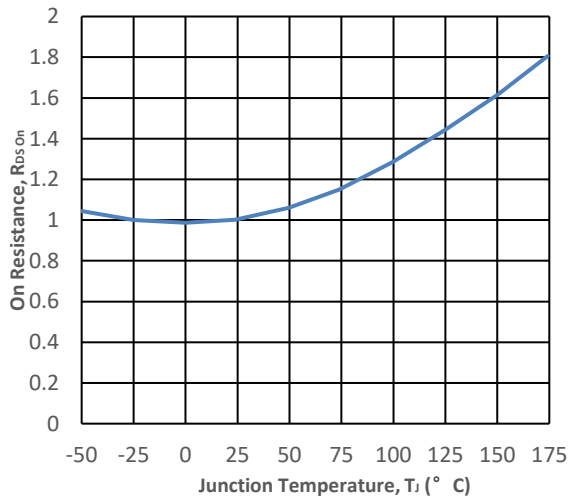
**Fig1. Output characteristics ( $T_J = 25^\circ\text{C}$ )**



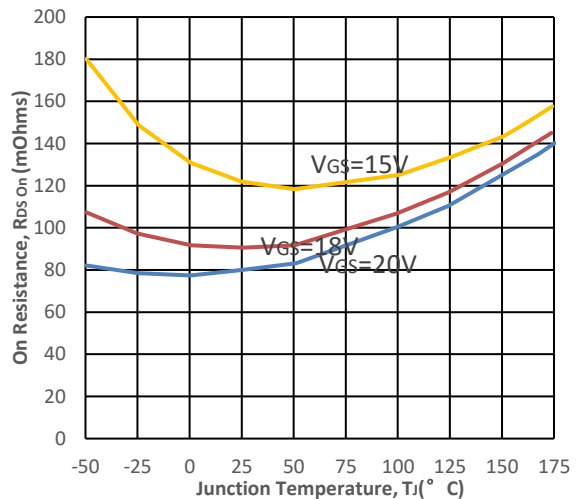
**Fig2. Output characteristics ( $T_J = 150^\circ\text{C}$ )**



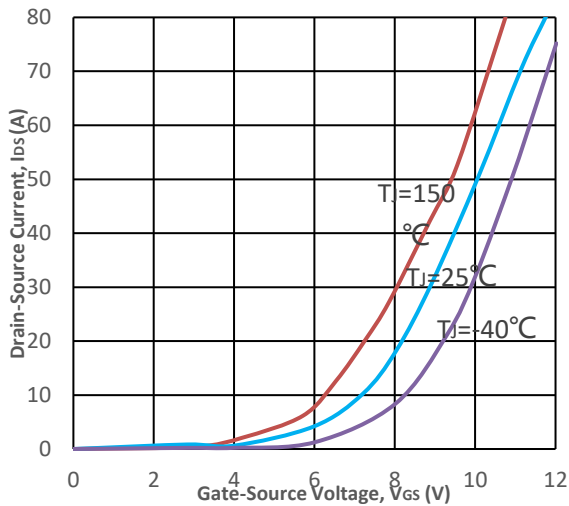
**Fig3. Normalized On-Resistance vs. Temperature**



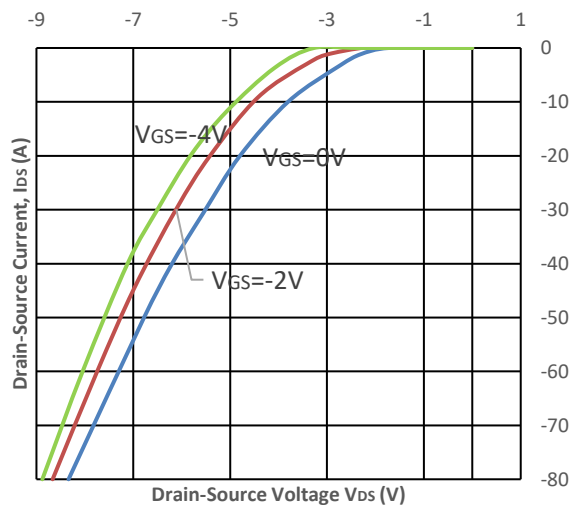
**Fig4. On-Resistance vs. Temperature**



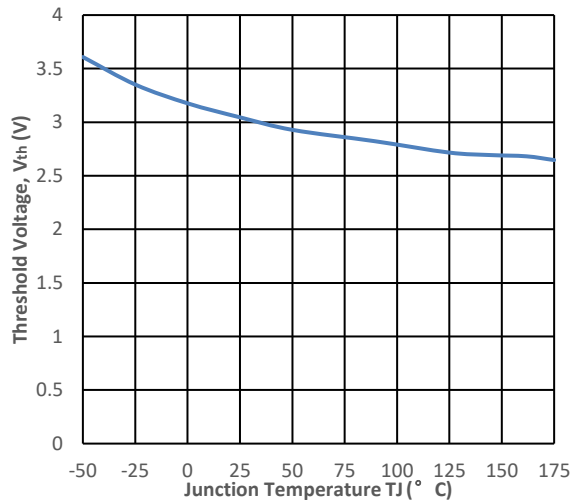
**Fig5. Transfer Characteristic**



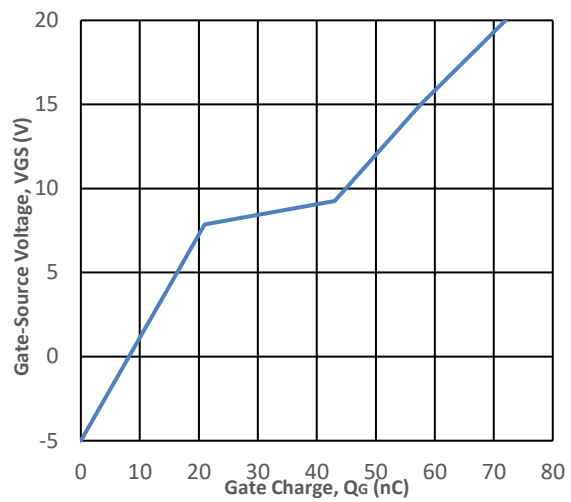
**Fig6. Body Diode Characteristic at  $25^\circ\text{C}$**



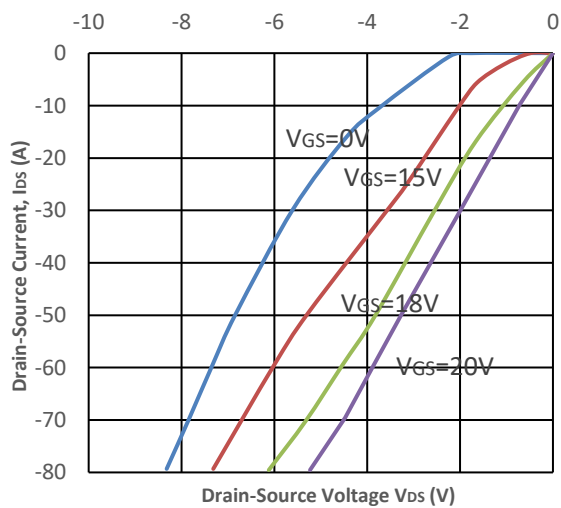
**Fig7. Threshold Voltage vs. Temperature**



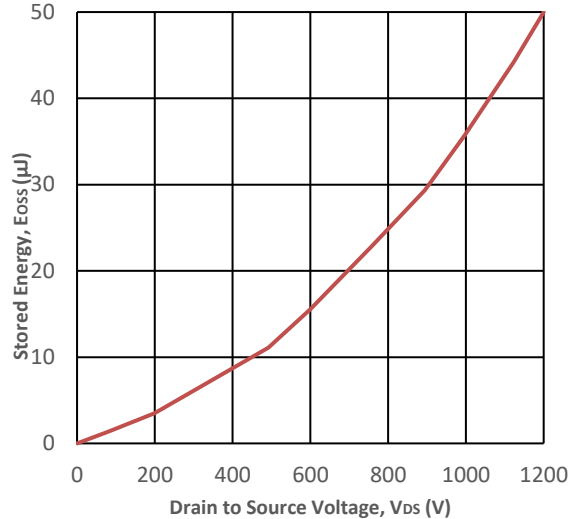
**Fig8. Gate Charge Characteristics**



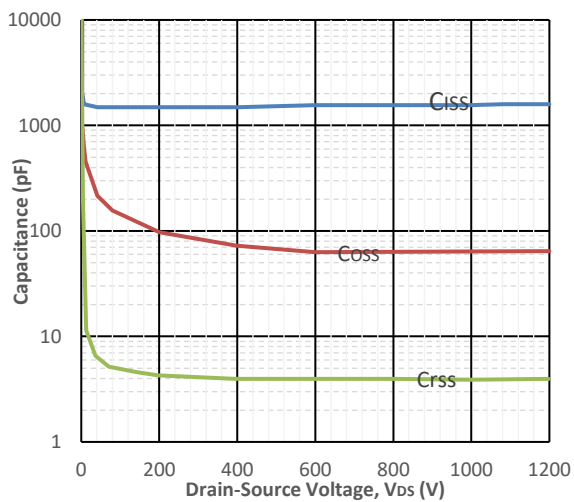
**Fig9. 3rd Quadrant Characteristic at 25  $^{\circ}$  C**



**Fig10. Output Capacitor Stored Energy**



**Fig11. Capacitances vs. Drain-Source**



**Fig12. Max Power Dissipation Derating Vs  $T_c$**

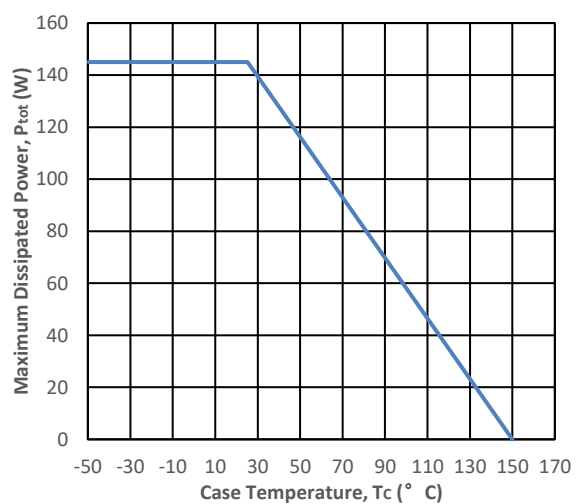


Fig13. Switching Energy vs. Drain Current

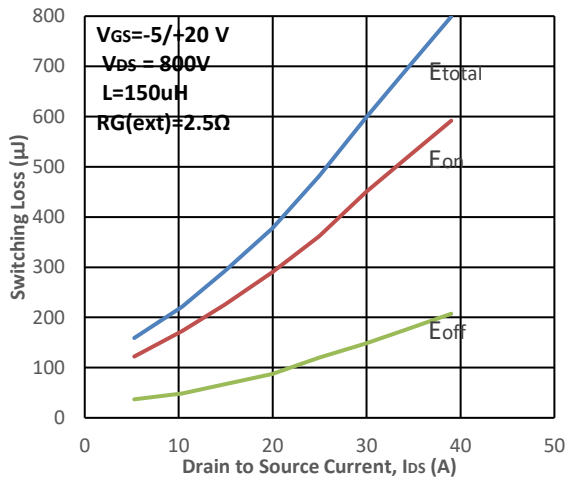


Fig14. Switching Energy vs.  $R_{G(\text{ext})}$

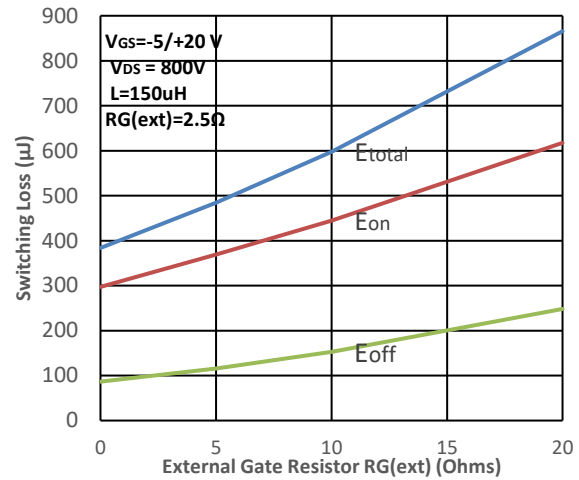


Fig15. Switching Energy vs. Temperature

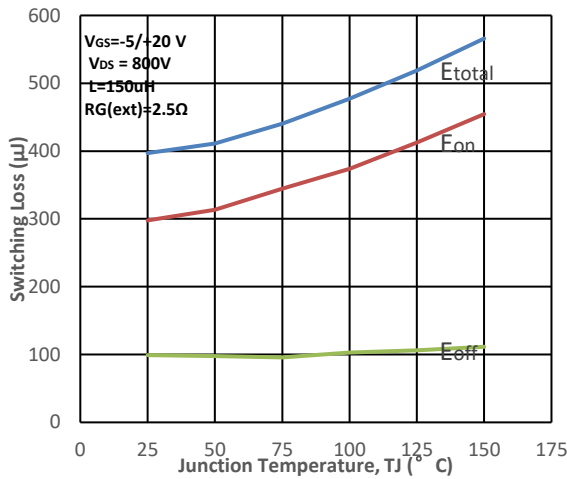


Fig16. Switching Times vs.  $R_{G(\text{ext})}$

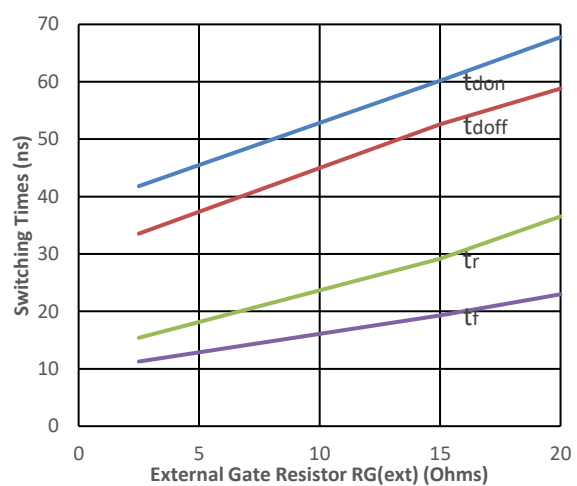


Fig17. Transient Thermal Impedance

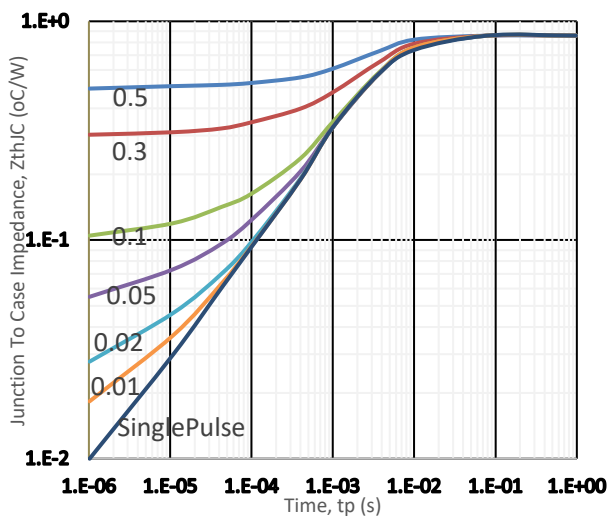
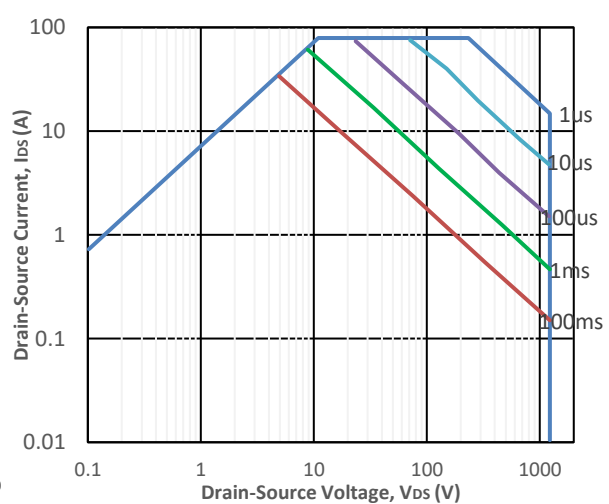
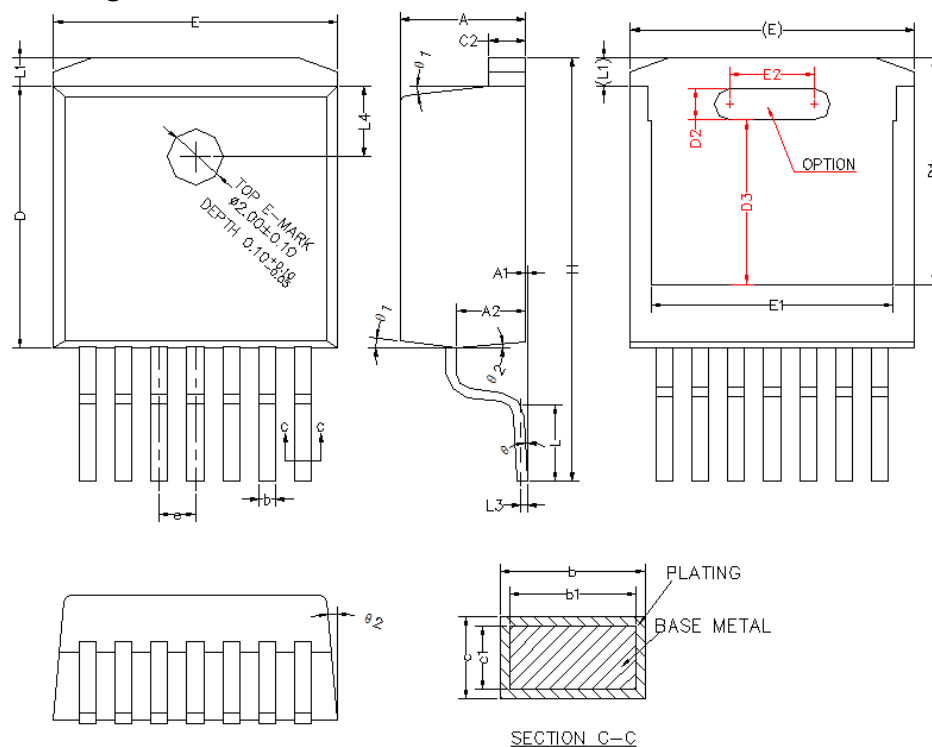


Fig18. Safe Operating Area



### Package Drawing:



### Dimensions ( UNIT: mm)

| SYMBOL     | MIN     | NOM   | MAX   |
|------------|---------|-------|-------|
| A          | 4.30    | 4.40  | 4.50  |
| A1         | 0.00    | 0.10  | 0.25  |
| A2         | 2.30    | 2.40  | 2.50  |
| b          | 0.56    | -     | 0.69  |
| b1         | 0.55    | 0.60  | 0.65  |
| c          | 0.37    | -     | 0.44  |
| c1         | 0.36    | 0.38  | 0.40  |
| c2         | 1.22    | 1.27  | 1.32  |
| D          | 9.15    | 9.25  | 9.35  |
| D1         | 7.90    | 8.00  | 8.10  |
| D2         | 1.00    | 1.11  | 1.20  |
| D3         | 5.70    | 5.80  | 5.90  |
| E          | 9.90    | 10.00 | 10.10 |
| E1         | 8.40    | 8.50  | 8.60  |
| E2         | 2.90    | 3.00  | 3.10  |
| e          | 1.17    | 1.27  | 1.37  |
| H          | 14.60   | 14.95 | 15.35 |
| L          | 2.40    | 2.70  | 2.90  |
| L1         | 0.90    | 1.00  | 1.10  |
| L3         | 0.25BSC |       |       |
| L4         | 2.50REF |       |       |
| $\theta$   | 0°      |       | 8°    |
| $\theta_1$ | 5°      | 7°    | 9°    |
| $\theta_2$ | 3°      | 5°    | 7°    |